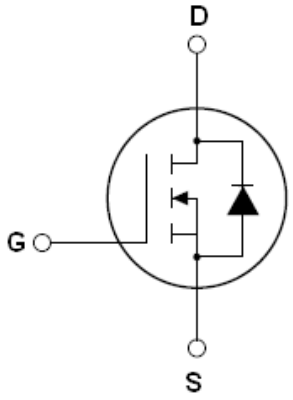
N-Channel Super Junction Power MOSFET Ⅱ

General Description

The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

V_{DS}	650	V
$R_{DS(ON)MAX}$	360	mΩ
I_D	11	A



Schematic diagram

Features

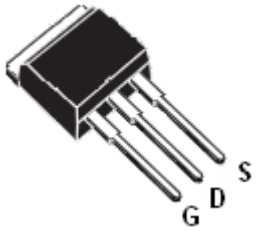
- New technology for high voltage device
- Low on-resistance and low conduction losses
- small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）

Package Marking And Ordering Information

Device	Device Package	Marking
TGD65R360U	TO-262	TGD65R360U



TO-262

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V)	V_{DS}	650	V
Gate-Source Voltage (V_{DS}=0V)	V_{GS}	±30	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	11	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	7	A
Pulsed drain current **(Note 1)**	$I_{DM\ (pluse)}$	33	A
Maximum Power Dissipation(Tc=25℃) Derate above 25°C	P_D	121 0.97	W W/°C
Single pulse avalanche energy **(Note2)**	E_{AS}	280	mJ
Avalanche current **(Note 1)**	I_{AR}	5.5	A
Repetitive Avalanche energy ， t_{AR} limited by T_{jmax} **(Note 1)**	E_{AR}	0.5	mJ

Parameter	Symbol	Value	Unit
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+150	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	1.03	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V		0.05	1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±30V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.5	3	3.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=7A		300	360	mΩ
Dynamic Characteristics						
Forward Transconductance	g_{FS}	V_{DS} = 20V, I_D = 7A		8		S
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		1030		pF
Output Capacitance	C_{oss}			87		pF
Reverse Transfer Capacitance	C_{rss}			4.5		pF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=11A, V_{GS}=10V		23	40	nC
Gate-Source Charge	Q_{gs}			5.7		nC
Gate-Drain Charge	Q_{gd}			8		nC
Intrinsic gate resistance	R_G	f = 1 MHz open drain		2		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=5.5A, R_G=6.8Ω,V_{GS}=10V		9		nS
Turn-on Rise Time	t_r			4		nS
Turn-Off Delay Time	$t_{d(off)}$			40	65	nS
Turn-Off Fall Time	t_f			4.5	8	nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			11	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				33	A
Forward on voltage	V_{SD}	Tj=25°C,I_{SD}=11A,V_{GS}=0V		0.9	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=11A,di/dt=100A/μs		245		nS
Reverse Recovery Charge	Q_{rr}			2.4		uC
Peak Reverse Recovery Current	I_{rrm}			20		A

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

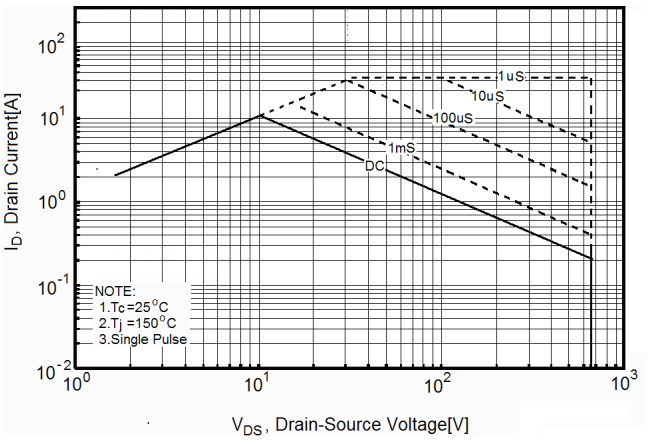


Figure2. Transient Thermal Impedance

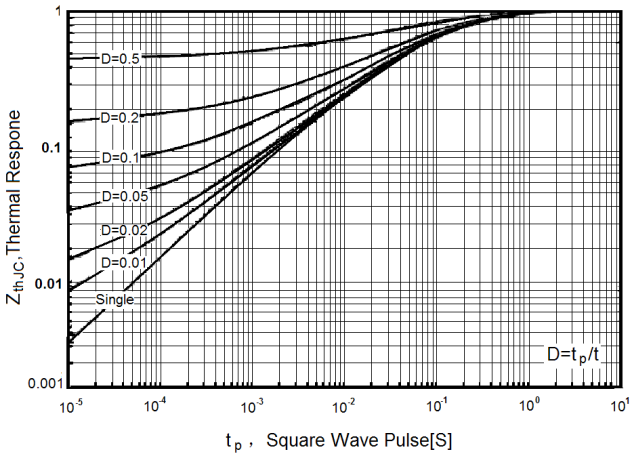


Figure3. Source-Drain Diode Forward Voltage

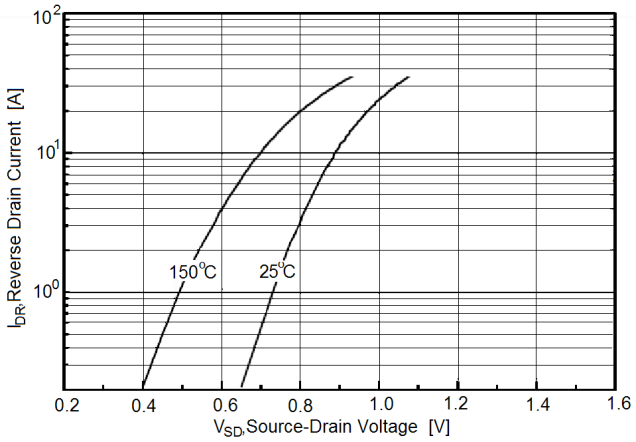


Figure4. Output characteristics

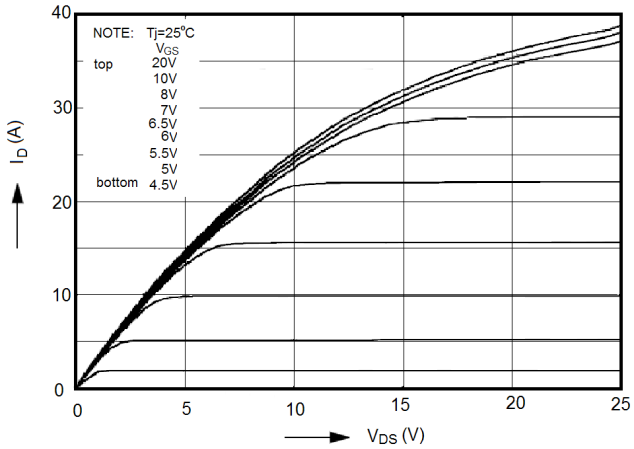


Figure5. Transfer characteristics

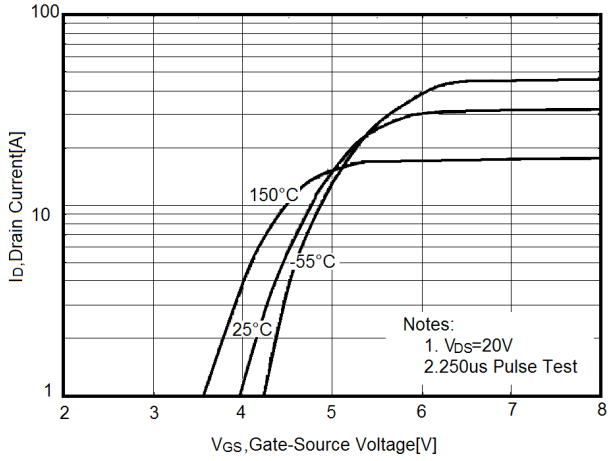


Figure6. Static drain-source on resistance

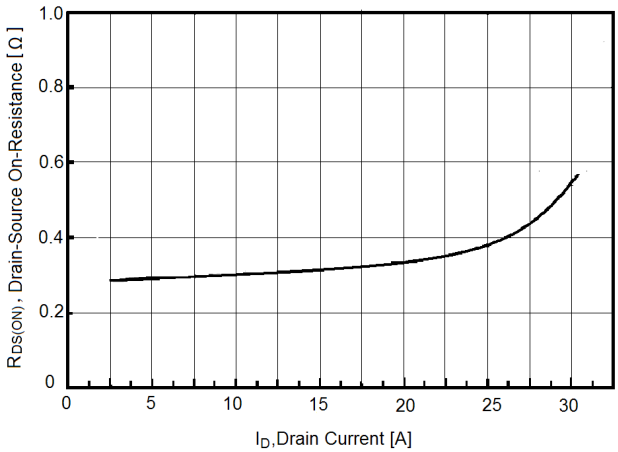


Figure7. $R_{DS(ON)}$ vs Junction Temperature

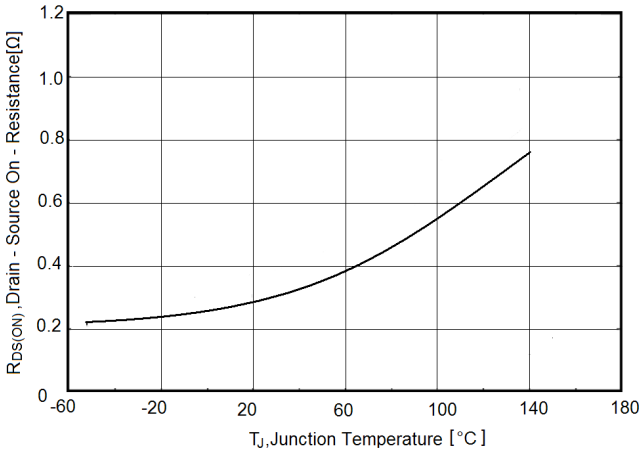


Figure8. BV_{DSS} vs Junction Temperature

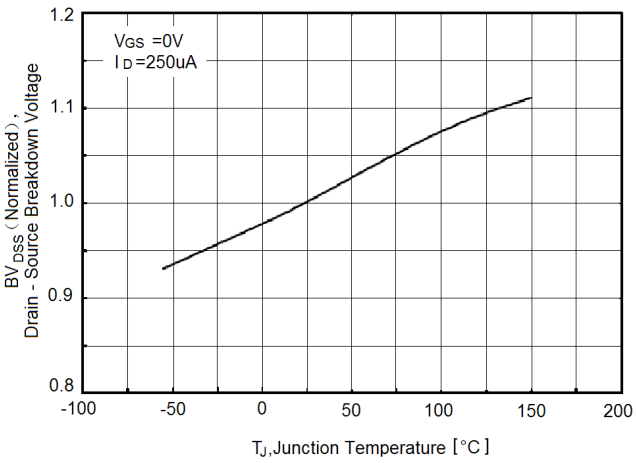


Figure9. Maximum I_D vs Junction Temperature

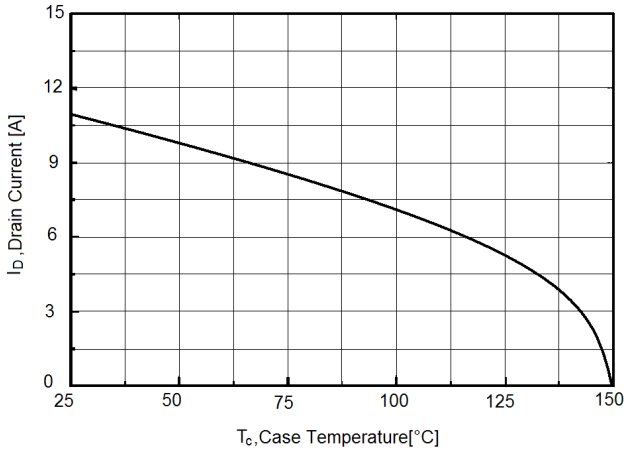


Figure10. Gate charge waveforms

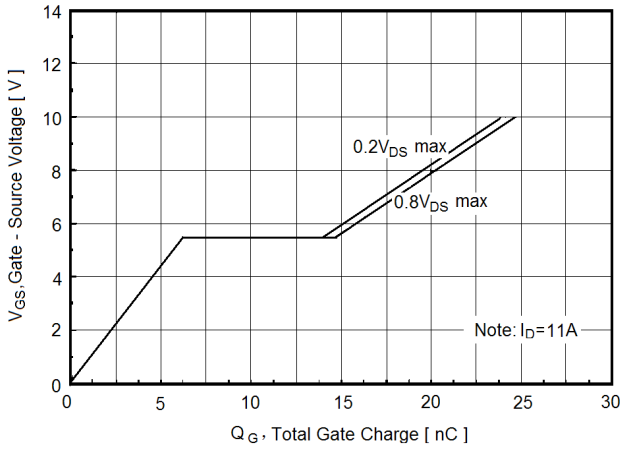
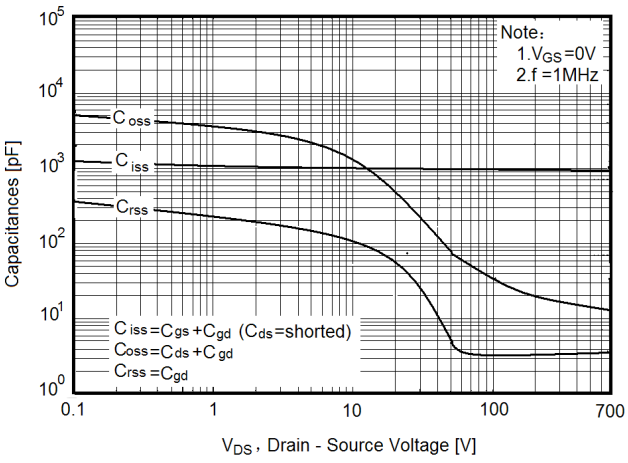
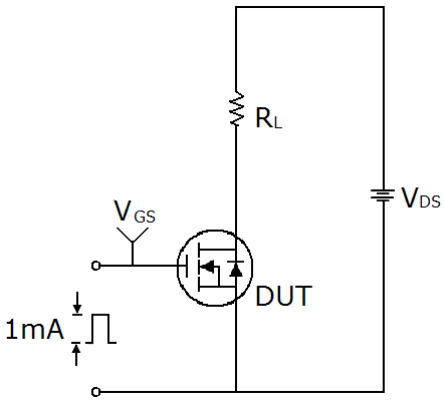


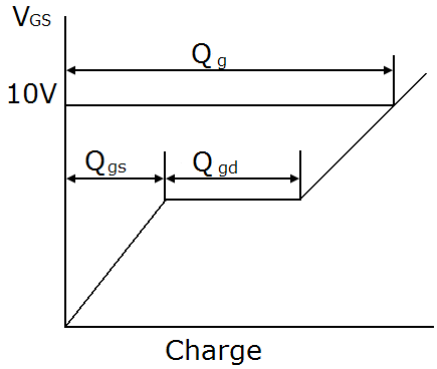
Figure11. Capacitance



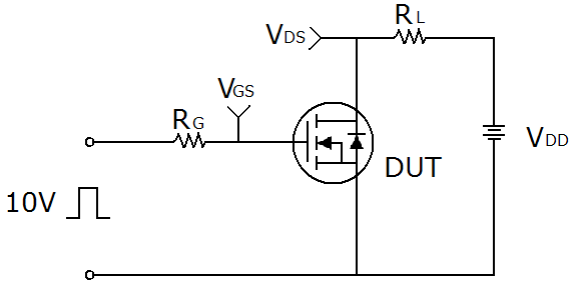
Test circuit

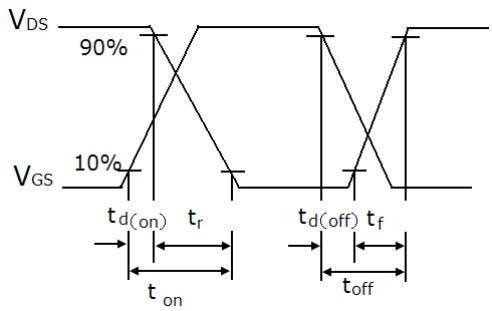
1）Gate charge test circuit & Waveform



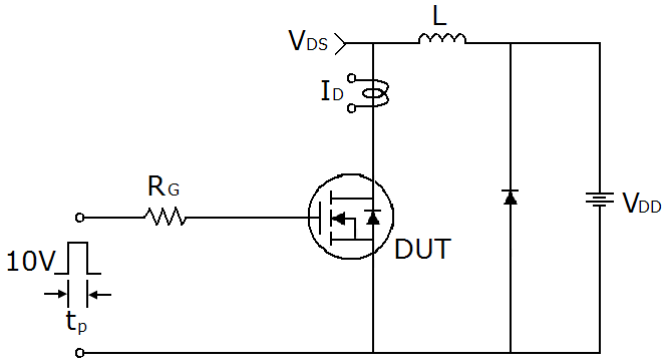


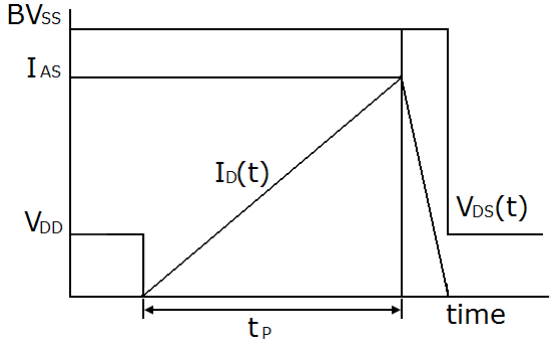
2）Switch Time Test Circuit：



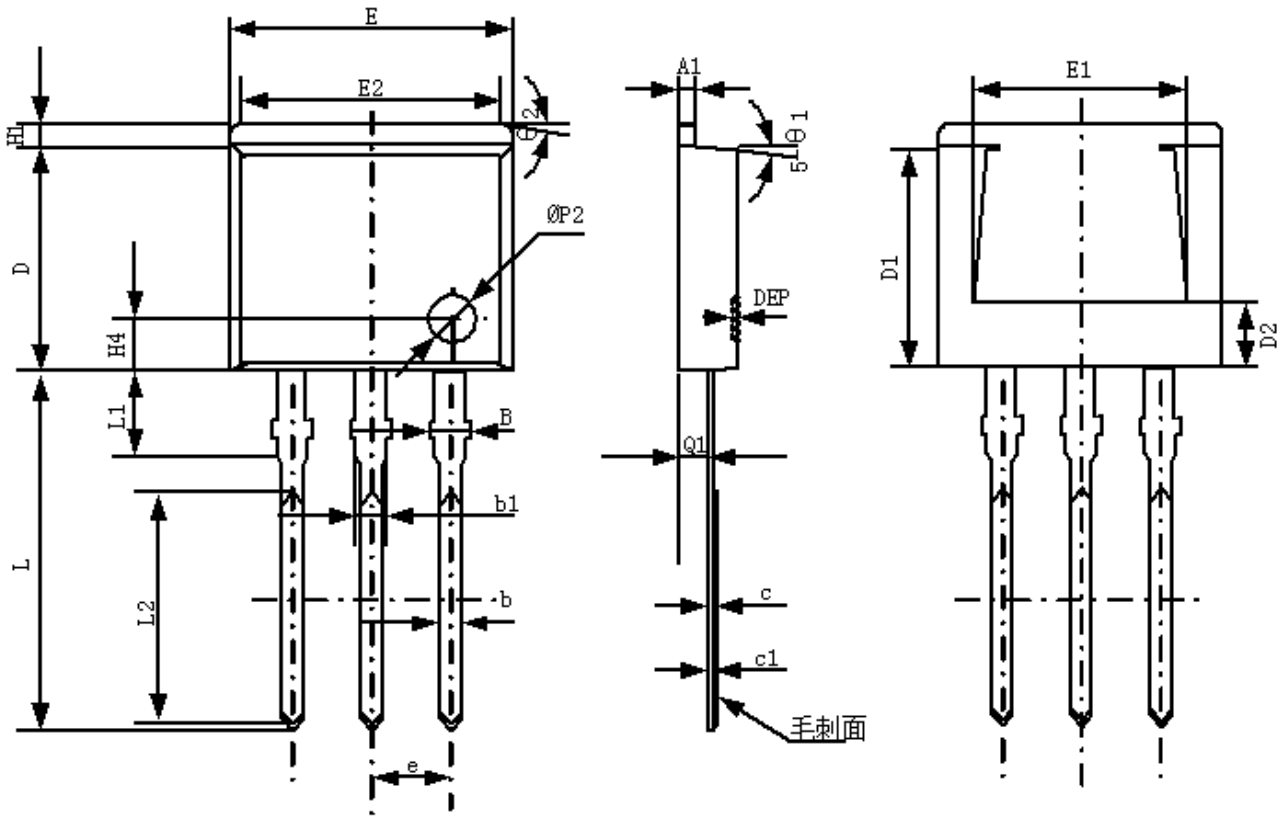


3）Unclamped Inductive Switching Test Circuit & Waveforms





TO-262 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
*A	4.600	4.800	0.182	0.190
A1	1.220	1.320	0.048	0.052
*b	0.763	0.863	0.030	0.034
b1	1.220	1.320	0.048	0.052
B	1.270	1.400	0.050	0.055
*c	0.330	0.430	0.013	0.017
*D	8.540	8.740	0.338	0.346
D1	8.200	8.400	0.324	0.332
D2	2.500	2.700	0.099	0.107
*E	10.10	10.30	0.399	0.407
E1	7.700	7.900	0.305	0.312
E2	8.340	9.340	0.330	0.369
H1	1.170	1.370	0.046	0.054
H4	2.100	2.300	0.083	0.091
*e	2.490	2.590	0.098	0.102
*L	13.66	14.06	0.540	0.556
L1	3.580	3.980	0.142	0.157
L2	8.660	8.860	0.342	0.350
*Q1	2.590	2.790	0.102	0.110